

AMENDMENTS TO THE CLAIMS

1-6. (Canceled)

7. (Previously presented) A semiconductor device comprising a fuse (3) having a fuse body (3A) and two pads (3Ba, 3Bb) connected by the fuse body (3A) and two conductive layers (5A, 5B) individually connected to two pads (3Ba, 3Bb), the above being formed inside a multilayer structure on a semiconductor substrate (1),

characterized in that a length (L1) of the fuse body (3A) is defined so that the melting location of the fuse (3) becomes positioned in the fuse body (3A) away from a region overlapped on the conductive layers (5A, 5B) when an electrical stress is applied between the two conductive layers (5A, 5B) to melt the fuse (3); and

in at least one of the above two conductive layers (5A, 5B), a distance (D4) from the contact regions (4A, 4B) connecting the conductive layers (5A, 5B) and the pads (3Ba, 3Bb) to edges of the pad (3Ba, 3Bb) contacting the fuse body (3A) is 0.25 μm to 0.90 μm .

8-15. (Canceled)

16. (Original) A semiconductor device comprising a fuse (3) including a conductive material in a multilayer structure on a semiconductor substrate (1), said fuse (3) having a fuse body (3A) and two pads (3Ba, 3Bb) connected by the fuse body (3A), conductive layers (5A, 5B) connected one by one to said two pads (3Ba, 3Bb),

characterized in that, in at least one of the above two conductive layers (5A, 5B), a width (W3) of the portions of the conductive layers (5A, 5B) including the contact regions (4A, 4B) with the pads (3Ba, 3Bb) is 6 μm to 14 μm .

17-18. (Canceled)

19. (Currently amended) A semiconductor device comprising:

a fuse body (3A) connected to a pad (3Ba), said fuse body (3A) including a fuse line (3Aa) and two connections (3Ab);

an inter-layer insulating film (4) on said pad (3Ba), an opening (4A) through said inter-layer insulating film (4) exposing said pad (3Ba);

a conductive layer (5A) on said inter-layer insulating film (4), said conductive layer (5A) within said opening (4A) being electrically connected to said pad (3Ba),

wherein at least one of the following is present:

(a) the width (W3) of said conductive layer (5A) is 6 μm to 14 μm ,

(b) the distance (D4) between said fuse line (3Aa) and said opening (4A) is 0.25 μm to 0.90 μm ,

(c) ~~said the~~ length (L1) of the fuse body (3A) is 1.8 μm to 20 μm .

20. (Currently amended) A semiconductor device as set forth in claim 19, wherein the melting location of ~~said~~ a fuse (3) becomes positioned in said fuse body (3A) away from a region overlapped on said conductive layer (5A) when an electrical stress to melt said fuse (3) is applied between said conductive layer (5A) and another conductive layer (5B).

21. (Previously presented) A semiconductor device as set forth in claim 19, wherein said width (W3) of said conductive layer (5A) is 6 μm to 14 μm .

22. (Previously presented) A semiconductor device as set forth in claim 19, wherein said distance (D4) between said fuse line (3Aa) and said opening (4A) is 0.25 μm to 0.90 μm .

23. (Previously presented) A semiconductor device as set forth in claim 19, wherein said length (L1) of the fuse body (3A) is 1.8 μm to 20 μm .

24. (Currently amended) A semiconductor device as set forth in claim 19, wherein said width (W3) is a dimension perpendicular to the direction of current flowing through ~~said~~ a fuse (3).

25. (Currently amended) A semiconductor device as set forth in claim 19, wherein said length (L1) is a dimension in the direction of current flowing through ~~said~~ a fuse (3), said length (L1) including the length (L0) of said fuse line (3Aa) and the lengths (L2) of said two connections (3Ab).

26. (Previously presented) A semiconductor device as set forth in claim 19, wherein another conductive layer (5B) within another opening (4A) through said inter-layer insulating film (4) is electrically connected to another pad (3Bb), the distance (D0) between said conductive layer (5A) and said another conductive layer (5B) is larger than said length (L1).

27. (Previously presented) A semiconductor device as set forth in claim 19, wherein one of the connections (3Ab) electrically connects said pad (3Ba) with fuse line (3Aa), said one of the connections (3Ab) being between said pad (3Ba) and said fuse line (3Aa).

28. (Previously presented) A semiconductor device as set forth in claim 19, wherein each of said two connections (3Ab) is wider than said fuse line (3Aa).

29. (Previously presented) A semiconductor device as set forth in claim 19, wherein a connection (3Ab) of said two connections (3Ab) has a width that increases toward said pad (3Ba).

30. (Previously presented) A semiconductor device as set forth in claim 19, wherein the width of the fuse body (3A) is smaller than the width (W3) of said pad (3Ba).

31. (Previously presented) A semiconductor device as set forth in claim 19, wherein one of the two connections (3Ab) electrically connects said pad (3Ba) with said fuse line (3Aa).

32. (Previously presented) A semiconductor device as set forth in claim 31, wherein another of the two connections (3Ab) electrically connects another pad (3Bb) with said fuse line (3Aa).

33. (Previously presented) A semiconductor device as set forth in claim 32, wherein another conductive layer (5B) within another opening (4A) through said inter-layer insulating film (4) is electrically connected to said another pad (3Bb), the distance (D0) between said conductive layer (5A) and said another conductive layer (5B) is larger than said length (L1).

34. (Previously presented) A semiconductor device as set forth in claim 33, wherein said length (L1) is the distance between said pad (3Ba) and said another pad (3Bb).